

Patent Application No. 09/681,643

IN THE CLAIMS:

Please renumber claims 11 and 12 to claims 17 and 18 as follows:

Claim 1. (previously presented) A manufacturing method of an active matrix device including a top gate type TFT, which comprises a process of forming the top gate type TFT, wherein the process of forming the top gate type TFT includes the steps of:

- 5 forming an oxide film on an inner wall of a CVD processing chamber;
arranging a substrate having source and drain electrodes formed therein in the processing chamber;
doping the source and drain electrodes with P;
forming an a-Si layer and a gate insulating film in the processing
10 chamber; and

wherein forming the oxide film on the inner wall of the CVD processing chamber is performed before doping the source and drain electrodes with P.

- Claim 2. (original) A manufacturing method of an active matrix device according to claim 1, wherein the process of forming the top gate type TFT further comprises the step of removing the oxide film from the inner wall after the step of forming the a-Si layer and the gate
5 insulating film.

Claim 3. (original) A manufacturing method of an active matrix device according to claim 1, wherein the oxide film contains SiOx.

Claim 4. (original) A manufacturing method of an active matrix device according to claim 1, wherein the active matrix device is a liquid crystal display.

Claim 5. (original) A manufacturing method of an active matrix device according to claim 1, wherein the active matrix device is an electroluminescence display.

Claim 6. (original) A manufacturing method of an active matrix device according to claim 2, wherein the oxide film contains SiOx.

Claim 7. (original) A manufacturing method of an active matrix device according to claim 2, wherein the active matrix device is a liquid crystal display.

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Claim 8. (original) A manufacturing method of an active matrix device according to claim 3, wherein the active matrix device is a liquid crystal display.

Claim 9. (original) A manufacturing method of an active matrix device according to claim 2, wherein the active matrix device is an electroluminescence display.

Claim 10. (original) A manufacturing method of an active matrix device according to claim 3, wherein the active matrix device is an electroluminescence display.

~~Claim 11.~~ Claim 17. (previously presented) A manufacturing method of an active matrix device according to claim 1, further comprising heating the inner wall of the CVD processing chamber.

~~Claim 12.~~ Claim 18. (previously presented) A manufacturing method of an active matrix device according to claim 1, wherein the oxide film is selected from the group consisting of SiOx, Al₂O₃, TiO₂, Al₂(Si₂O₅)(OH)₄, MgAl₂O₄, TaOx, and ZrOx.